

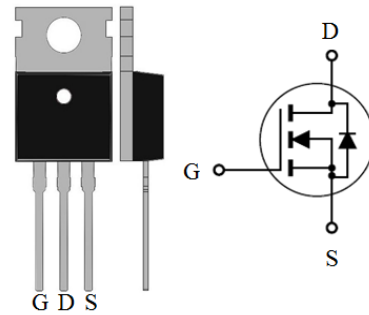
100V N-Channel MOSFET
Applications:

- Uninterruptible Power Supply
- High Speed Power Switching
- High Efficiency Synchronous Rectification in SMPS

V_{DS}	$R_{DS(ON)}(MAX)$	I_D
100V	8m Ω	115A

Features:

- Lead Free
- Low $R_{DS(ON)}$ to Minimize Conductive Loss
- Low Gate Charge for Fast Switching Application
- Optimized $V_{(BR)DSS}$ Ruggedness



TO220 Pin Definition and Inner Circuit

Ordering Information

Park Number	Package	Brand
MXP1008AT	TO220	MXP

Absolute Maximum Ratings
 $T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-to-Source Voltage	100	V
I_D	Continuous Drain Current	Silicon Limited	115
		Package Limited	80
I_{DM}	Pulsed Drain Current @ $V_{GS}=10V$	459	
P_D	Power Dissipation	242	W
V_{GS}	Gate-to-Source Voltage	+/-20	V
T_J and T_{stg}	Operating Junction and Storage Temperature Range	-55 to 175	$^\circ\text{C}$

Avalanche Characteristics
 $T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Unit
$E_{AS}^{\text{①}}$	Single Pulse Avalanche Energy ($V_{DS}=50V$, $V_{GS}=10V$, $R_g=25\Omega$, $L=1mH$)	200	mJ
I_{AS}	Single Pulse Avalanche Current	Figure 9	A

Thermal Resistance

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.62	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	$^\circ\text{C}/\text{W}$

① : Guarantee number.

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OFF Characteristics
 $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	-	-	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	-	-	1	μA	$V_{DS}=80V, V_{GS}=0V$
		-	-	100		$V_{DS}=80V, V_{GS}=0V, T_J=125^{\circ}\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	-	-	100	nA	$V_{GS}=+20V$
	Gate-to-Source Reverse Leakage	-	-	100		$V_{GS}=-20V$

ON Characteristics
 $T_J=25^{\circ}\text{C}$ unless otherwise specified

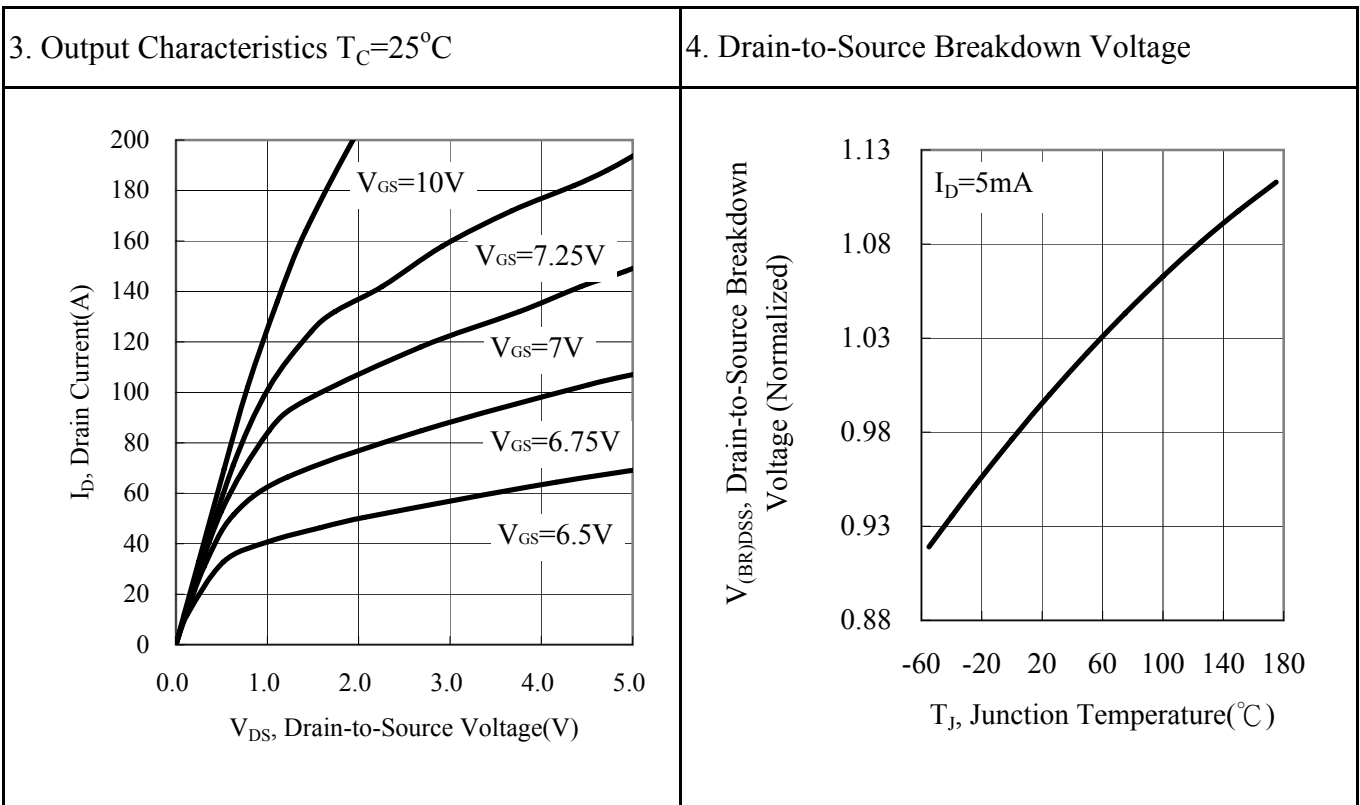
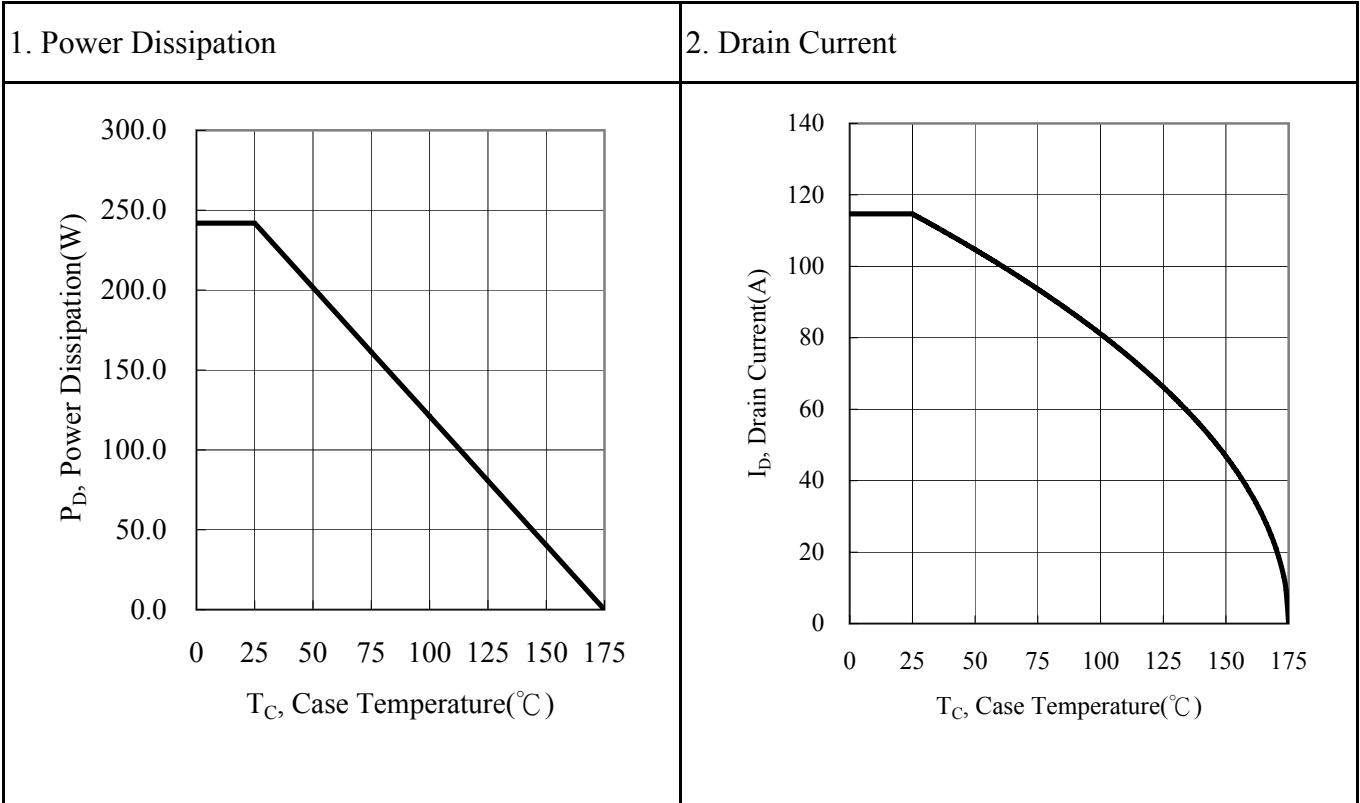
Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	-	6.3	8.0	$m\Omega$	$V_{GS}=10V, I_D=69A$
$V_{GS(th)}$	Gate Threshold Voltage	2.5	-	4.5	V	$V_{GS}=V_{DS}, I_D=250\mu A$

Dynamic Characteristics
 $T_J=25^{\circ}\text{C}$ unless otherwise specified

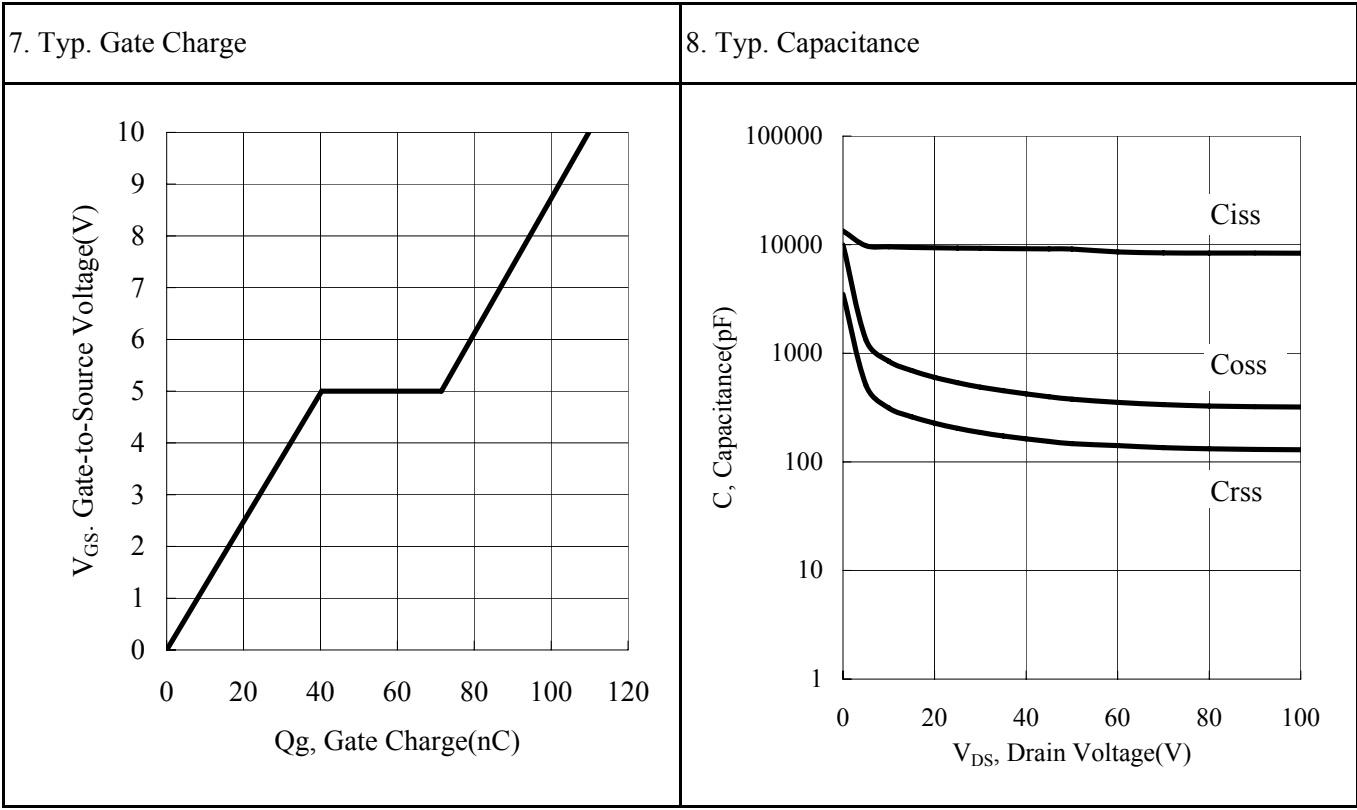
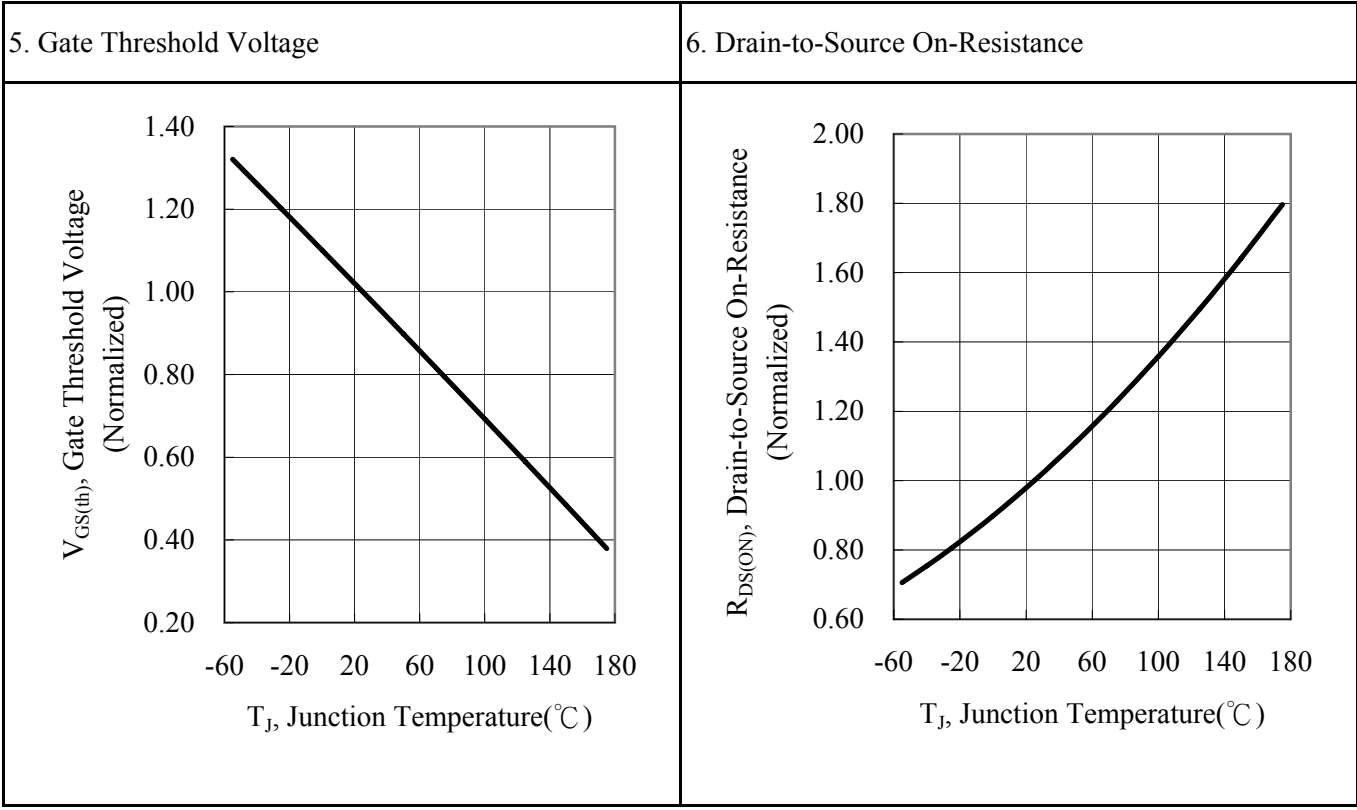
Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
C_{iss}	Input Capacitance	-	9315	-	pF	$V_{GS}=0V, V_{DS}=25V,$ $f=1.0MHz$
C_{oss}	Output Capacitance	-	536	-		
C_{rss}	Reverse Transfer Capacitance	-	204	-		
Q_g	Total Gate Charge	-	110	-	nC	$V_{DD}=50V, I_D=69A, V_{GS}=10V$
Q_{gs}	Gate-to-Source Charge	-	40	-		
Q_{gd}	Gate-to-Drain ("Miller") Charge	-	31	-		
$T_d(on)$	Turn-on Delay Time	-	51	-	ns	$V_{DD}=50V, I_D=35A, V_{GS}=10V$ $R_G=10\Omega, R_L=1.4\Omega$
T_r	Rise Time	-	130	-		
$T_d(off)$	Turn-off Delay Time	-	107	-		
T_f	Fall Time	-	51	-		

Source-Drain Diode Characteristics
 $T_J=25^{\circ}\text{C}$ unless otherwise specified

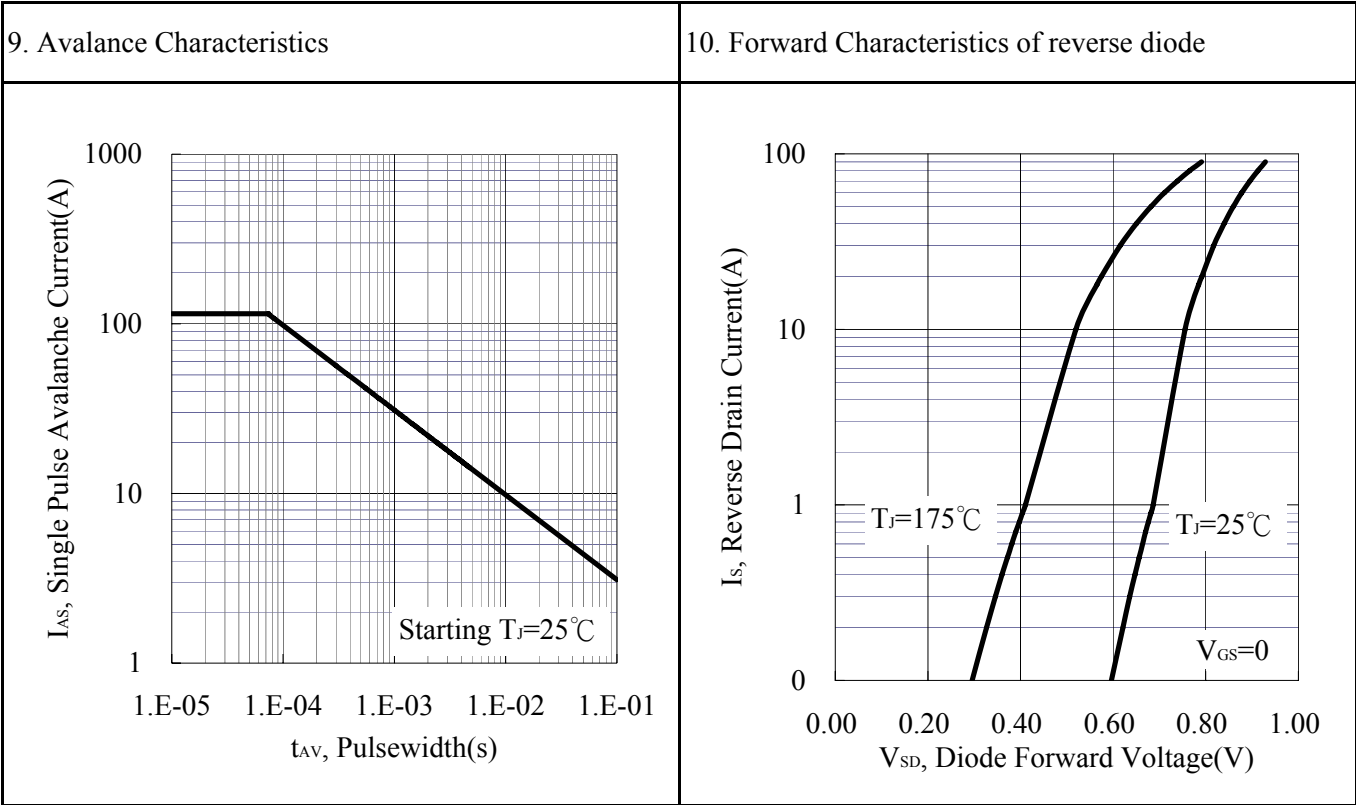
Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
V_{SD}	Diode Forward Voltage	-	-	1.2	V	$I_S=69A, V_{GS}=0V$
T_{rr}	Reverse Recovery Time	-	86.8	-	ns	$I_S=69A, di/dt=100A/\mu s$
Q_{rr}	Reverse Recovery Charge	-	229.3	-	nC	

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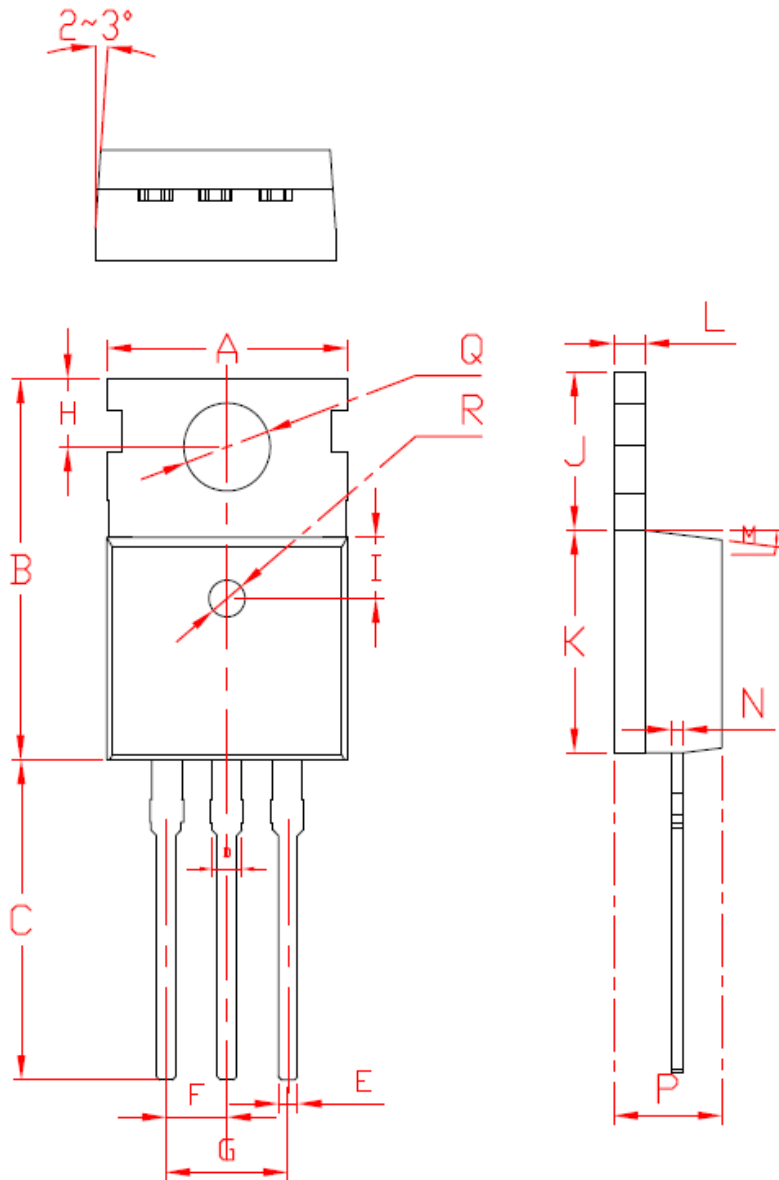


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TO220

1. Outline Dimension



Symbol	A	B	C	D	E	F	G	H	I	J	K	L	M	N	O	P	Q	R
Min	9.8	15.4	12.75					2.73		6.4	9	1.29		0.48	2.35	4.4	3.5	1.4
Non	10	15.6	13.1	1.31	0.8	2.54	5.08	2.8	2.5	6.5	9.1	1.3	1.27	0.5	2.4	4.5	3.6	1.5
Max	10.2	15.8	13.17					2.87		6.6	9.2	1.32		0.56	2.5	4.7	3.63	1.6

UNIT : mm

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